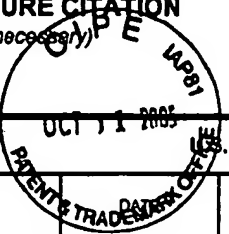


<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>				ATTY DOCKET NO. <b>YOR920030602US1 (17242)</b>		APPLICATION NO. <b>10/725,850</b>		
				APPLICANT(S) <b>Joel P. de Souza et al.</b>				
				FILING DATE <b>December 2, 2003</b>		GROUP ART UNIT <b>2818</b>		
<b>U.S. PATENT DOCUMENTS</b>								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
<i>dlh</i>		5,384,473	01/24/1995	Yoshikawa et al.				
<i>dlh</i>		6,815,278 B1	11/09/2004	leong et al.				
<b>U.S. PATENT APPLICATION PUBLICATIONS</b>								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
<i>dlh</i>		2005/0016290	06/02/2005	deSouza et al.				
<b>FOREIGN PATENT DOCUMENTS</b>								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>								
<i>dlh</i>		Csepregi, L. et al., Substrate-orientation dependence of the epitaxial regrowth rate from Si-implanted amorphous Si, 49:7 <i>J. Appl. Phys.</i> 3906, 3906-10, (1978);						
<i>dlh</i>		6th International Symposium on Semiconductor Wafer Bonding, <i>An investigation into interfacial oxide in direct silicon bonding</i> , (September 2001); and						
EXAMINER <i>[Signature]</i>				DATE CONSIDERED <i>03/13/06</i>				
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>								

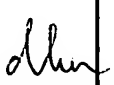
<b>INFORMATION DISCLOSURE CITATION</b> (Use several sheets if necessary)				ATTY DOCKET NO. <b>YOR920030602US1 (17242)</b>		APPLICATION NO. <b>10/725,850</b>	
				Joel P. de Souza et al.			
				FILING <b>December 2, 2005</b>		GROUP ART <b>2818</b>	

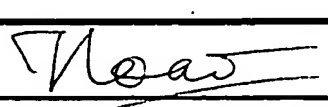


U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE		

U.S. PATENT APPLICATION PUBLICATIONS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	

FOREIGN PATENT DOCUMENTS								
DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION			
					YES	NO		

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
			Solid State Technology, <i>SOI wafers based on epitaxial technology</i> , (2000), available at <a href="http://sst.pennnet.com/articles/article_display.cfm?Section=ARCHI&amp;Feat&amp;ARTICLE_ID75323&amp;KEYWORDS=K%2E%20Sakaguchi&amp;p=5">http://sst.pennnet.com/articles/article_display.cfm?Section=ARCHI&amp;Feat&amp;ARTICLE_ID75323&amp;KEYWORDS=K%2E%20Sakaguchi&amp;p=5</a>

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